



DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C		
20V	$24m\Omega @ V_{GS} = 4.5V$	6.2A		
	$28m\Omega$ @ $V_{GS} = 2.5V$	5.7A		

Features and Benefits

- Low Gate Threshold Voltage
- Low On-Resistance
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.

https://www.diodes.com/quality/product-definitions/

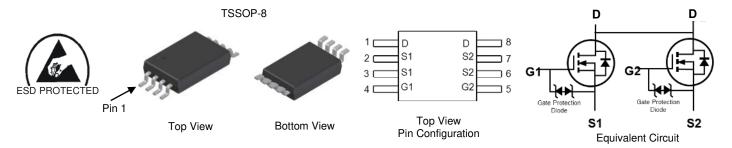
Description and Applications

This MOSFET is designed to minimize the on-state resistance (RDS(ON)) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- Battery Management Application
- Power Management Functions
- DC-DC Converters

Mechanical Data

- Case: TSSOP-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208³
- Weight: 0.039 grams (Approximate)



Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2024UTS-13	TSSOP-8	2500/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



O':| = Manufacturer's Marking N2024U = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 20 = 2020) WW = Week (01 to 53)



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	VDSS	20	V		
Gate-Source Voltage	V _{GSS}	±10	V		
Continuous Drain Current (Note C) V 4 EV	Steady State	T _A = +25°C T _A = +70°C	ΙD	6.2 4.9	А
Continuous Drain Current (Note 6) V _{GS} = 4.5V	Steady State	T _C = +25°C T _C = +70°C	lo	15.2 12.1	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%	I _{DM}	45	Α		
Maximum Continuous Body Diode Forward Current	Is	1.6	Α		
Pulsed Source-Drain Diode Current (10µs Pulse, D	lsм	45	Α		
Avalanche Current (Note 7) L = 0.1mH	las	12	Α		
Avalanche Energy (Note 7) L = 0.1mH	Eas	8	mJ		

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

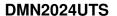
Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$	P_{D}	0.89	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	RеJA	140	°C/W
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	1.39	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Rеja	90	°C/W
Thermal Resistance, Junction to Case (Note 6)	Steady State	Rejc	15	C/VV
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

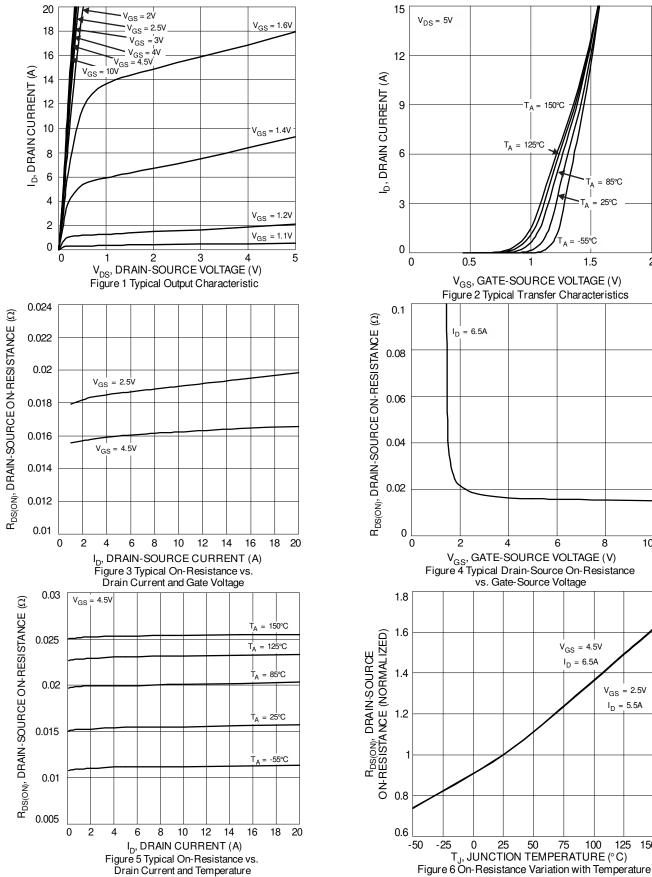
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Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage		20	-	_	٧	$V_{GS} = 0V, I_{D} = 250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	_	_	1	μΑ	$V_{DS} = 20V$, $V_{GS} = 0V$	
Gate-Source Leakage	Igss	_	_	±10	μΑ	$V_{GS} = \pm 8V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS} (TH)	0.35	1	0.95	٧	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	Dagger		16	24	mΩ	$V_{GS} = 4.5V, I_{D} = 6.5A$	
Static Drain-Source Off-Nesistance	R _{DS(ON)}		18	28	11122	$V_{GS} = 2.5V, I_D = 5.5A$	
Diode Forward Voltage	V _{SD}	_	0.7	1.0	V	V _G S = 0V, I _S = 1A	
DYNAMIC CHARACTERISTICS (Note 9)						•	
Input Capacitance	Ciss	_	647	_	рF		
Output Capacitance	Coss	_	78	_	рF	$V_{DS} = 10V, V_{GS} = 0V,$ - f = 1.0MHz	
Reverse Transfer Capacitance	Crss	_	38	_	рF	1 = 1.0WHZ	
Gate Resistance	Rg	_	400	_	Ω	Ω V _{DS} = 0V, V _{GS} = 0V, f = 1MHz	
Total Gate Charge (V _{GS} = 4.5V)	Q _G	_	6.5	_	nC		
Total Gate Charge (V _{GS} = 10V)	QG	_	14.8	_	nC	\/ 10\/ I- 0.5A	
Gate-Source Charge	Q _{GS}	_	1.1	_	nC	$V_{DS} = 10V, I_{D} = 6.5A$	
Gate-Drain Charge	Q _{GD}	_	1.7	_	nC	1	
Turn-On Delay Time	td(ON)	_	98	_	ns		
Turn-On Rise Time	t _R	_	140	_	ns	$V_{DS} = 10V, V_{GS} = 4.5V,$	
Turn-Off Delay Time	tD(OFF)	_	1024	_	ns	$R_G = 6\Omega$, $R_L = 10\Omega$, $I_D = 1A$	
Turn-Off Fall Time	tF	_	434	_	ns	7	
Reverse Recovery Time		_	245	_	ns	L 10 di/dt 1000/	
Reverse Recovery Charge	Qrr	_	149	_	nC	I _F = 1A, di/dt = 100A/µs	

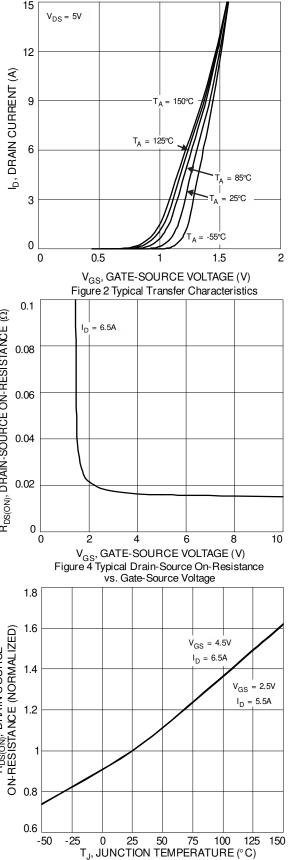
Notes:

- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
- I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.

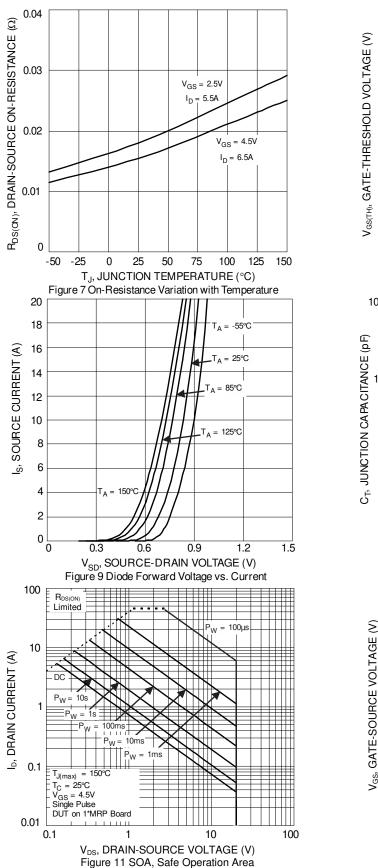


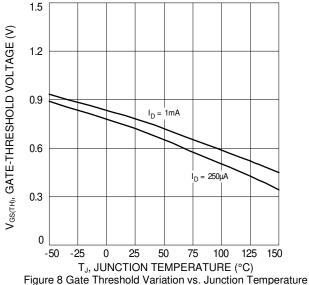












f=1MHz

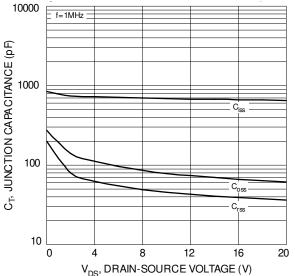
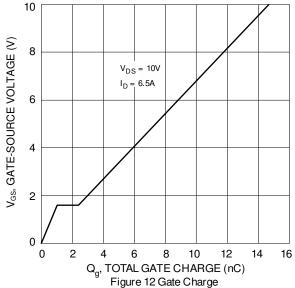


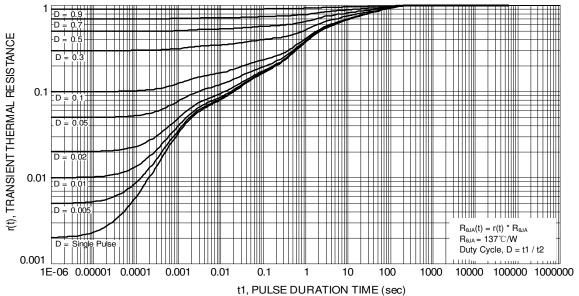
Figure 10 Typical Junction Capacitance



April 2020

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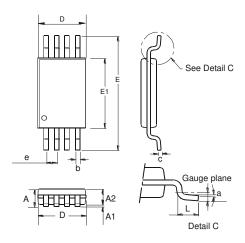
t1, PULSE DURATION TIME (sec) Figure 13 Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TSSOP-8

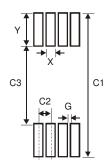


TSSOP-8					
Dim	Min	Max	Тур		
а	0.09	-	-		
Α	_	1.20	-		
A 1	0.05	0.15	_		
A2	0.825	1.025	0.925		
b	0.19	0.30	_		
С	0.09	0.20	-		
D	2.90	3.10	3.025		
е	-	_	0.65		
Е	-	_	6.40		
E1	4.30	4.50	4.425		
Ĺ	0.45	0.75	0.60		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

TSSOP-8



Dimensions	Value (in mm)
Х	0.45
Υ	1.78
C1	7.72
C2	0.65
C3	4.16
G	0.20



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